

**REMARKS**

Claims 1-11 and 21-25 are pending and at issue in this application. Of the claims at issue, claims 1 and 21 are independent. In the official action dated April 13, 2004, claims 1-11 were rejected as unpatentable over Yin et al. (U.S. Pat. No. 6,586,820). In view of the foregoing amendments and the following remarks, the rejections are respectfully traversed and reconsideration of this application is respectfully requested.

As an initial matter, the applicant notes that the official action allowed claims 7-11 if rewritten in independent form. By way of this amendment, claims 21-25 have been added. Independent claim 21 corresponds to claim 7 rewritten in independent form, and claims 22-25 are dependent on claim 21. Accordingly, claims 21-25 are in condition for allowance and are not discussed further herein.

In amended FIG. 1, the previously omitted descriptive legend “(Prior Art)” has been added. No new matter has been added.

Turning to the art rejections, the applicant respectfully submits that claim 1 is patentable over the art cited in the Office action. Claim 1 recites a method that performs a plasma treatment to form a plurality of adjacent grooves on an upper surface of a stacking structure, wherein the grooves are configured to increase adhesion between the upper surface of the stacking structure and a photoresist layer. None of the cited references, whether taken alone or in combination, teaches or suggests such a method.

While Yin et al. generally disclose fabricating semiconductor devices, there is no teaching or suggestion of performing a plasma treatment to form a plurality of adjacent grooves on an upper surface of a stacking structure, wherein the grooves are configured to increase adhesion between the upper surface of the stacking structure and a photoresist

**U.S. Serial No. 10/636,030  
Attorney Docket No. 20067/OPP030888US**

layer. Instead, Yin et al. simply disclose treating an anti-reflective coating of a silicon structure with gaseous plasma or a solution of sulfuric acid and hydrogen peroxide but without forming a plurality of grooves on an upper surface of the silicon structure. *See* Yin et al., FIGS. 6 and 7. Therefore, Yin et al. do not teach or suggest the method recited in claim 1. Accordingly, claim 1 and all claims dependent thereon are now in condition for allowance.

For these reasons, it is respectfully submitted that claims 1-11 and 21-25 are in condition for allowance. If, for any reason, the examiner is unable to allow the application in the next official action, the examiner is encouraged to telephone the undersigned attorney at the telephone number listed below.

The Commissioner is authorized to charge any fee deficiency required by this paper, or credit any overpayment, to Deposit Account No. 50-2455. A copy of this paper is enclosed.

Respectfully submitted,

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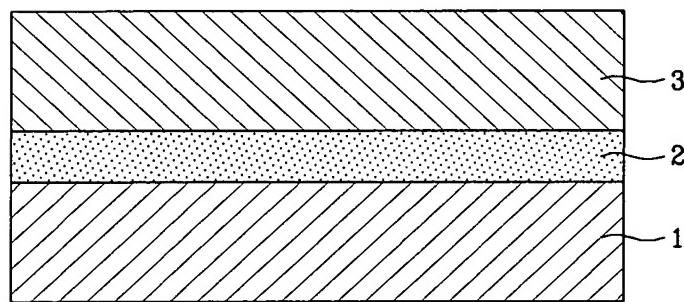
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U.S. Serial No. 10/363,030  
Attorney Docket No. 20067/OP030888US  
Response to the Office Action dated April 13, 2004  
Annotated Sheet Showing Changes

*FIG. 1 (Prior Art)*



*FIG. 2*

